

Rev.F Mar.-2016

TO-3P

Schottky Barrier Diode in a TO-3P Plastic Package.

Low forward voltage drop, low power losses, High efficiency operation.

OR-ing

DC-DC

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RWM} V_{DC}	200	V
RMS Reverse Voltage	V_{RMS}	140	V
Average forward current	$I_{F(AV)}$	2×15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Ambient case	$R_{\theta Jc}$	1.4	/W
Operating and Storage Temperature Range	T_j T_{stg}	-40 +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V_{BR}	$I_R=1mA(T_a=25^\circ C)$	200			V
Forward Voltage	V_F	$I_F=5A(T_a=25^\circ C)$		0.73	0.85	V
		$I_F=10A(T_a=25^\circ C)$		0.80	0.95	V
		$I_F=15A(T_a=25^\circ C)$		0.92	1.15	V
		$I_F=5A(T_a=125^\circ C)$		0.58		V
		$I_F=10A(T_a=125^\circ C)$		0.66		V
		$I_F=15A(T_a=125^\circ C)$		0.71	0.85	V
Instantaneous Reverse current (Note 1)	I_R Note 1	$V_R=200V(T_a=25^\circ C)$		4	20	μA
		$V_R=200V(T_a=125^\circ C)$		5	10	mA

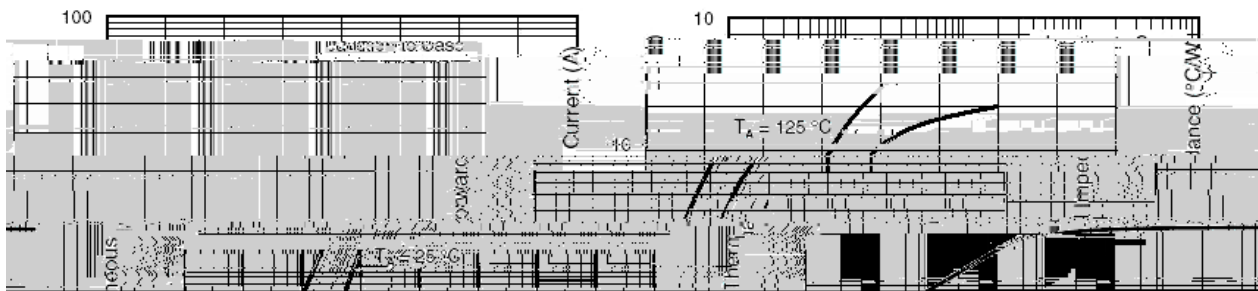
/Notes

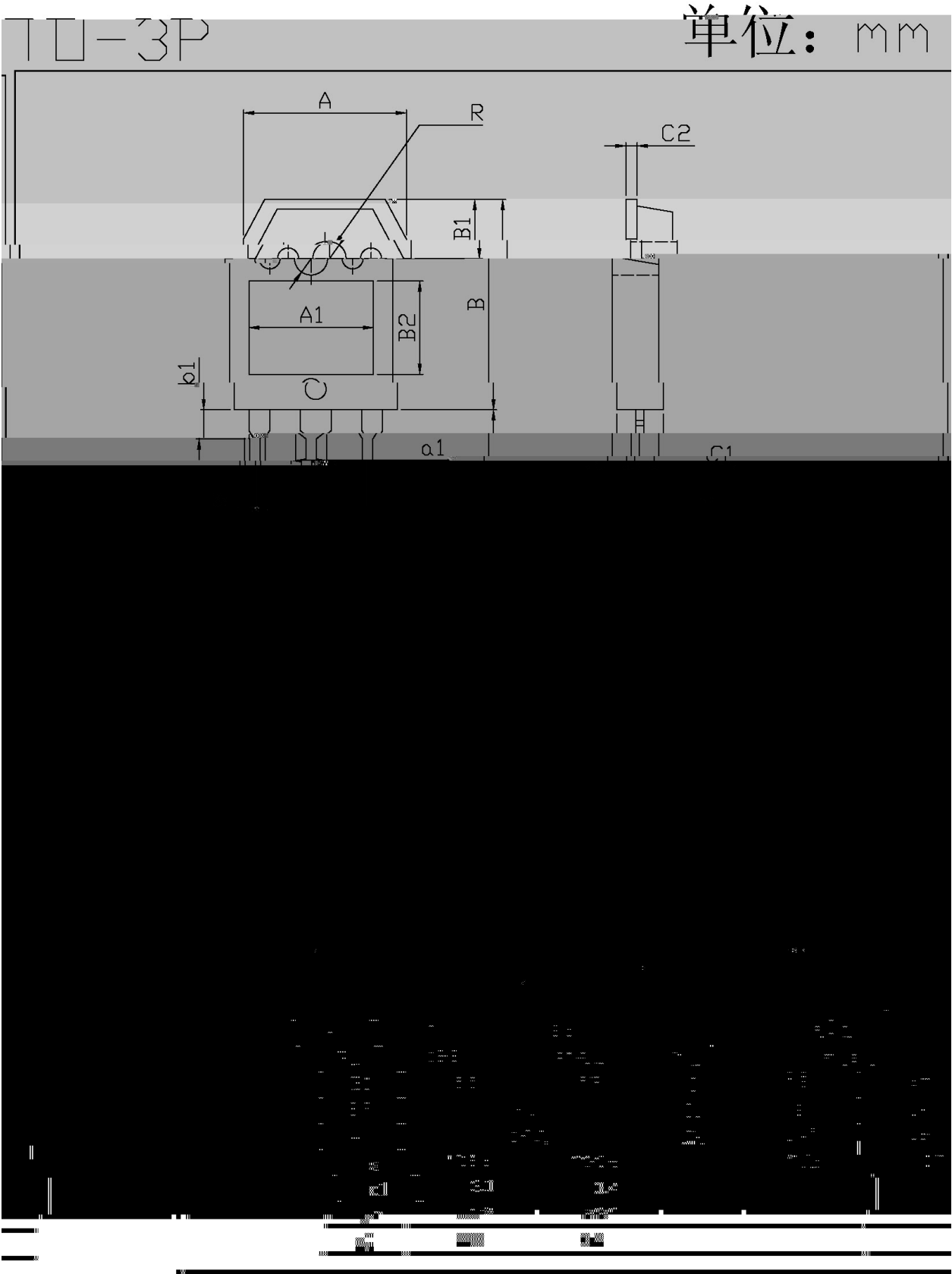
 1.
effect.

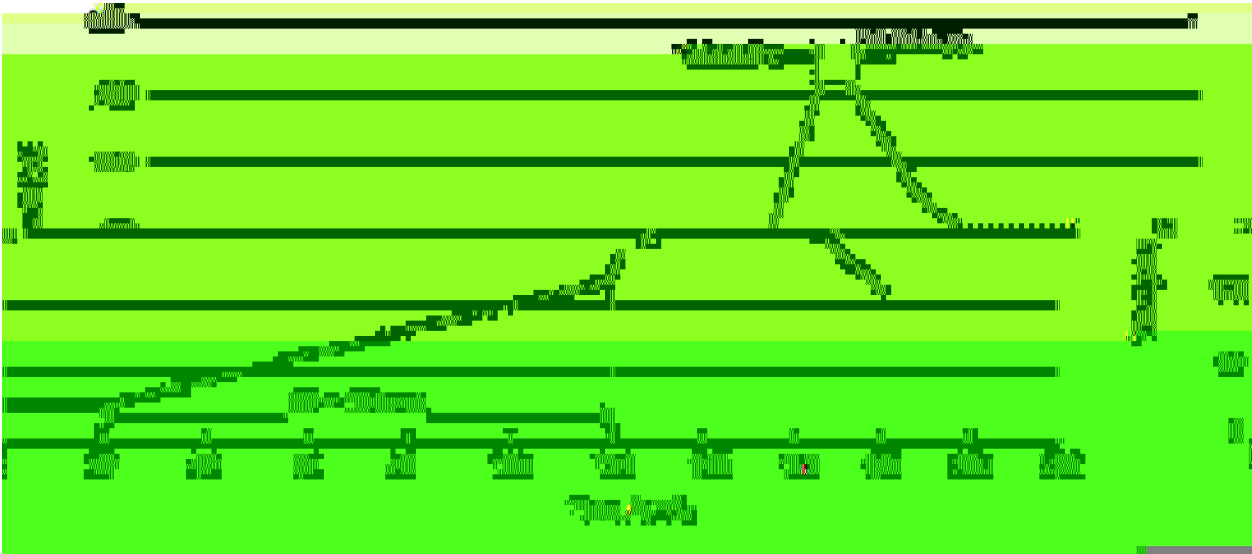
/Short duration pulse test used to minimize self-heating

 2.
single chip.

/ Unless otherwise noted, values for the parameters of a







Note:			
1	25 150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5	5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10	/sec.	3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5